

## Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

$$I_{FAV} = 85 \text{ A}$$

$$V_F = 1.1 \text{ V}$$

Phase leg

Part number

**MDMA85P1200TG**



Backside: isolated

 E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		2	mA
$V_F$	forward voltage drop	$I_F = 85$ A		$T_{VJ} = 25^\circ\text{C}$		1.15	V
		$I_F = 170$ A				1.38	V
		$I_F = 85$ A		$T_{VJ} = 125^\circ\text{C}$		1.10	V
		$I_F = 170$ A				1.39	V
$I_{FAV}$	average forward current	$T_C = 100^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		85	A
		rectangular	$d = 0.5$				
$V_{F0}$	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.79	V
$r_F$	slope resistance					3.5	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.35	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.2		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		350	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.50	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.62	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		1.28	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.38	kA
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		11.3	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		10.9	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		8.13	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		7.87	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		60	pF



Package TO-240AA				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			200	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>					76	g	
$M_D$	mounting torque		2.5		4	Nm	
$M_T$	terminal torque		2.5		4	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	13.0	9.7		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
$V_{ISOL}$	isolation voltage	t = 1 second		4800		V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V	



**Part description**

- M = Module
- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 85 = Current Rating [A]
- P = Phase leg
- 1200 = Reverse Voltage [V]
- TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA85P1200TG	MDMA85P1200TG	Box	36	513015

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}\text{C}$



**Rectifier**

$V_{0\ max}$	threshold voltage	0.79	V
$R_{0\ max}$	slope resistance *	2.3	mΩ



Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



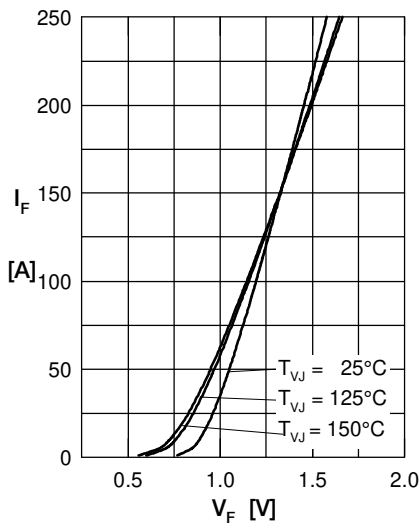
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

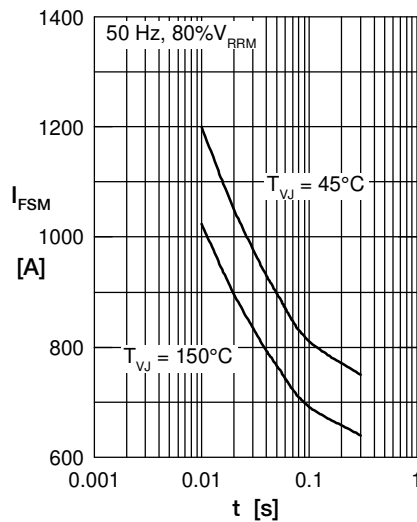


Fig. 2 Surge overload current vs. time per diode

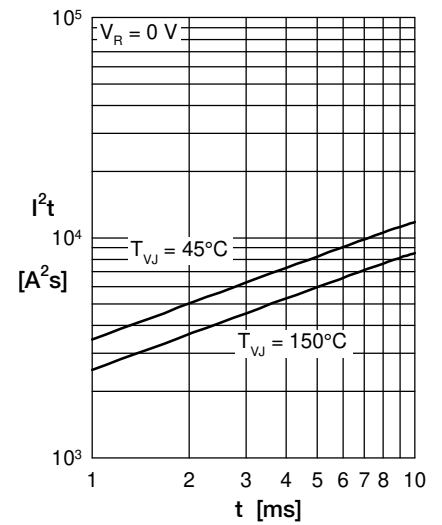
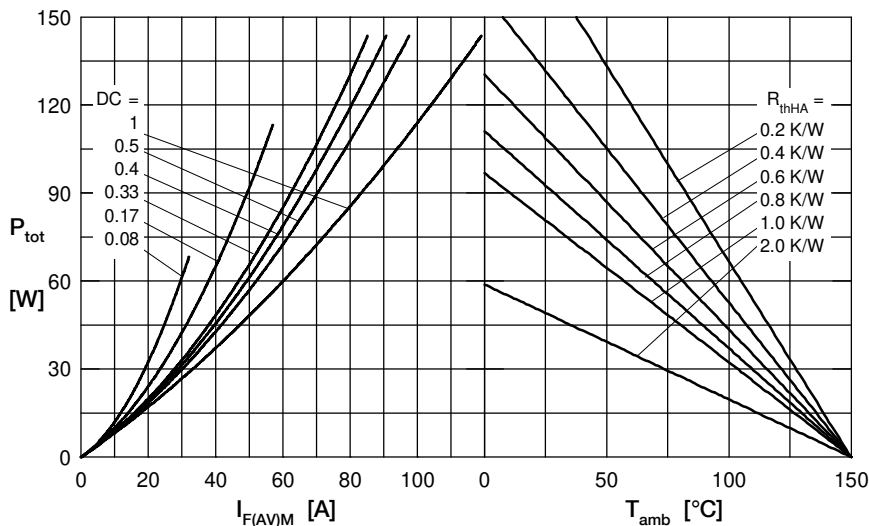

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

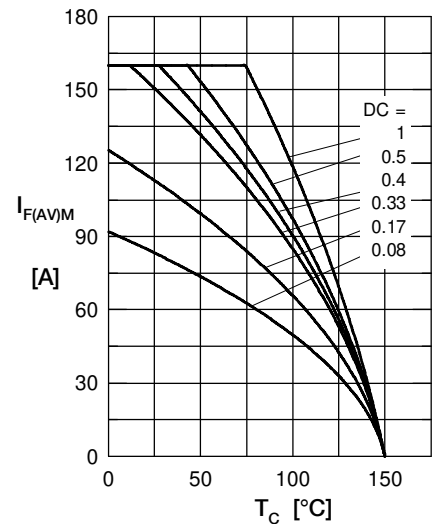


Fig. 5 Max. forward current vs. case temperature per diode

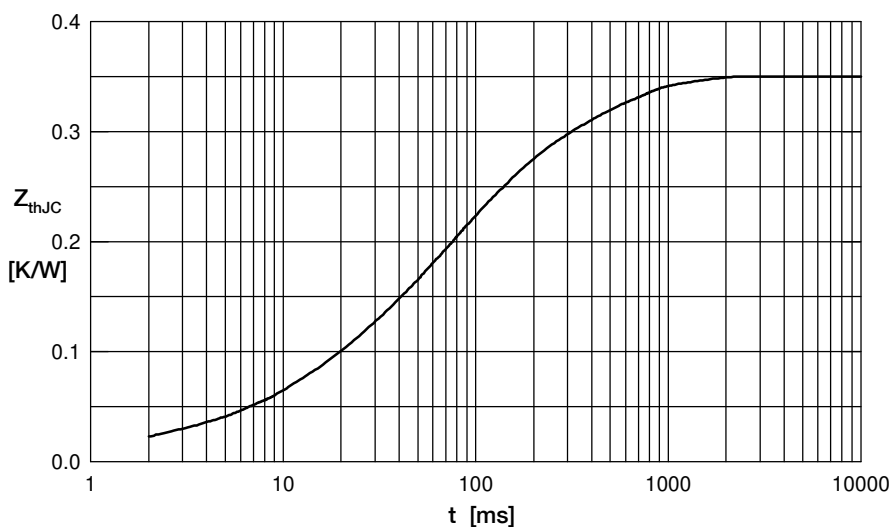


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.012	0.001
2	0.048	0.013
3	0.185	0.070
4	0.105	0.400